VS-HFA08TB120SPbF

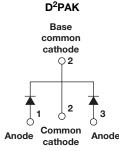
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FREE

HEXFRED[®], Ultrafast Soft Recovery Diode, 8 A



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PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK)					
I _{F(AV)}	8 A					
V _R	1200 V					
V _F at I _F	3.3 V					
t _{rr} (typ.)	28 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
 AEC-Q101 gualified
- AEC-Q101 qualifiedMaterial categorization:
- For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		130	А					
Maximum repetitive forward current	I _{FRM}		32						
Maximum power dissipation	р	T _C = 25 °C	73.5	W					
	P _D	T _C = 100 °C	29	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

Revision: 27-Aug-12

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Document Number: 94046

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage		I _F = 8.0 A	-	2.6	3.3	v			
	V _{FM}	I _F = 16 A	-	3.4	4.3				
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1				
Maximum reverse		V _R = V _R rated	-	0.31	10				
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	-	135	1000	μA			
Junction capacitance	CT	V _R = 200 V	-	11	20	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V _R = 30 V	-	28	-	ns		
	t _{rr1}	T _J = 25 °C		-	63	95			
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/µs	-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A nC		
	I _{RRM2}	T _J = 125 °C		-	6.2	11			
	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	140	380			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880			
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-	A∕µs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	Tlead	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	r\/ vv			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking device		Case style D ² PAK		HFA08	FB120S				

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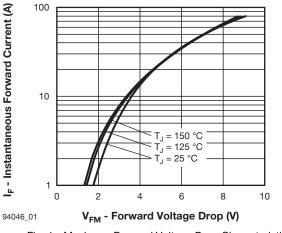
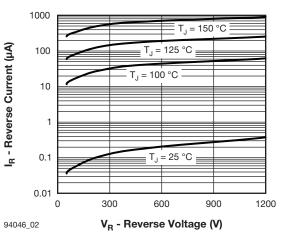
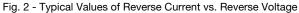


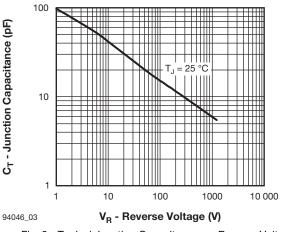
Fig. 1 - Maximum Forward Voltage Drop Characteristics

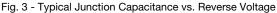
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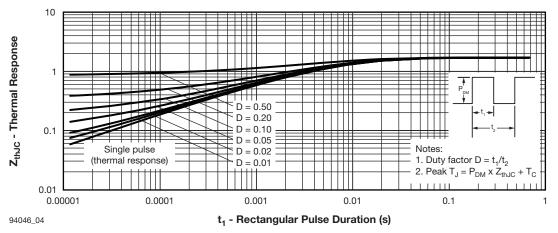


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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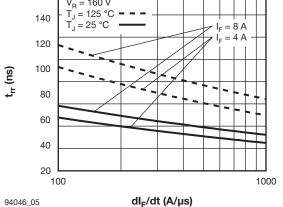


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

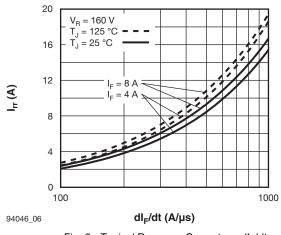
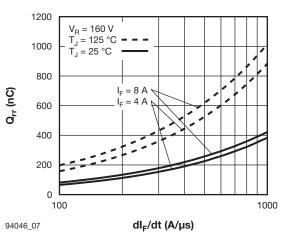


Fig. 6 - Typical Recovery Current vs. dl_F/dt

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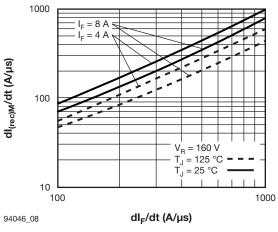


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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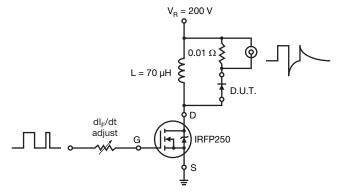
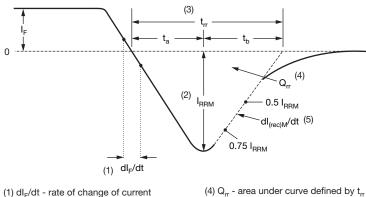
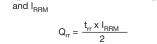


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



- (5) dI_{(rec)M}/dt peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$
- Fig. 10 Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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Device code	VS-	HF	Α	08	тв	120	S	TRL	PbF		
	1	2	3	4	5	6	7	8	9		
	 Vishay Semiconductors product HEXFRED[®] family 										
	3 -	Process designator: A = Electron irradiated									
	4 -	Cur	Current rating (08 = 8 A)								
	5 -	Pac	kage ou	utline (Tl	B = TO-	220, 2 I	eads)				
	6 -	Volt	age rati	ng (120	= 1200	V)					
	7 -	S =	D ² PAK								
	8 -	• No	one = T	ube							
		 TRL = Tape and reel (left oriented) 									
		• TF	RR = Ta	pe and	reel (rig	ht orien	ted)				
	9 -	• Pł	oF = Lea	ad (Pb)-	free						
		• P	= Lead	(Pb)-fre	e (for D	² PAK T	RR and	TRL)			

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)								
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCR								
VS-HFA08TB120SPBF	50	1000	Antistatic plastic tube					
VS-HFA08TB120STRRP	800	800	13" diameter reel					
VS-HFA08TB120STRLP	800	800	13" diameter reel					

VS-HFA08TB120SPbF

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Outline Dimensions

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MIN.

0.270

0.380

0.311

0.575

0.070

0.050

0.188

0.100 BSC

0.010 BSC

MAX.

0.315

0.420

0.346

0.625

0.110

0.070

0.208

3

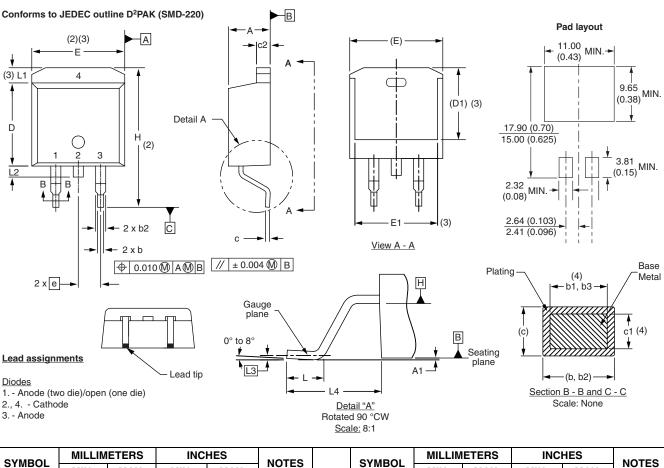
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3

D²PAK





SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	
С	0.38	0.74	0.015	0.029		L1	-	1.65	
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

 $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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